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APPLICANT(S):

YING ZHOU, ET AL.

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**U.S. PATENT DOCUMENTS**

*EXAMINE R INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.						
	B.						
	C.						
	D.						
	E.						
	F.						
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	H.						
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**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	J.							
	K.							
	L.							
	M.							
	N.							
	O.							

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

<i>me</i>	P.	Robert M. Wallace, "Challenges for the Characterization and Integration of High-k Gate Dielectrics," pp. 1-50, Nov. 2002, <a href="http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf">http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf</a>
<i>me</i>	Q.	Gerry Lucovsky, "The Physics and Chemistry of High-k Dielectrics and their Interfaces," pp. 1-49, available on June 2003, at <a href="http://www.sematech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf">http://www.sematech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf</a>
	R.	
	S.	
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EXAMINER

*Michelle Estrada*

DATE CONSIDERED

*9/27/04*

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